



## 2SB1132

## PNP SILICON TRANSISTOR

### MEDIUM POWER TRANSISTOR

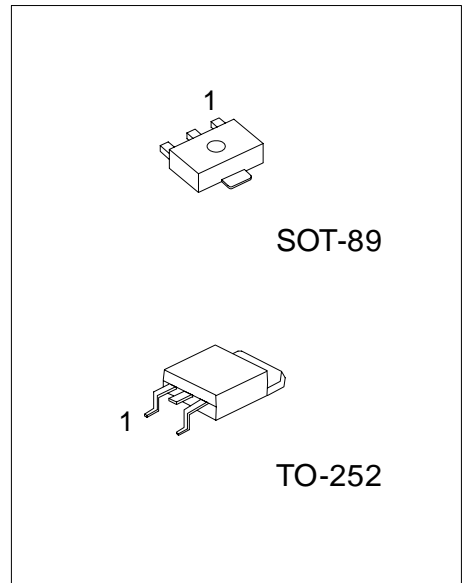
#### DESCRIPTION

The UTC 2SB1132 is a epitaxial planar type PNP silicon transistor.

#### FEATURES

\* Low  $V_{CE(SAT)}$ .

$V_{CE(SAT)} = -0.2V(Typ.) (I_C/I_B = -500mA/-50mA)$



\*Pb-free plating product number: 2SB1132L

#### ORDERING INFORMATION

Order Number		Package	Pin Assignment			Packing
Normal	Lead Free Plating		1	2	3	
2SB1132-x-AB3-R	2SB1132L-x-AB3-R	SOT-89	B	C	E	Tape Reel
2SB1132-x-TN3-R	2SB1132L-x-TN3-R	TO-252	B	C	E	Tape Reel
2SB1132-x-TN3-T	2SB1132L-x-TN3-T	TO-252	B	C	E	Tube

<p>2SB1132L-x-AB3-R</p> <p>(1)Packing Type (2)Package Type (3)Rank (4)Lead Plating</p>	<p>(1) R: Tape Reel, T: Tube (2) AB3: SOT-89, TN3: TO-252 (3) x: refer to Classification of <math>h_{FE}</math> (4) L: Lead Free Plating, Blank: Pb/Sn</p>
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■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector-Base Voltage	V <sub>CBO</sub>	-40	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-32	V
Emitter-Base Voltage	V <sub>EBO</sub>	-5	V
Collector Current	DC	-1	A
Collector Current (Single pulse, Pw=100ms)	PULSE		
Collector Power Dissipation	SOT-89	0.5	W
	TO-252	1	W
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature	T <sub>STG</sub>	-55 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (Ta=25°C, unless otherwise specified)

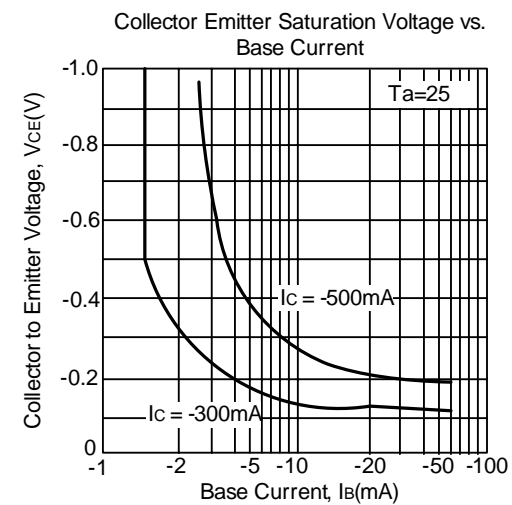
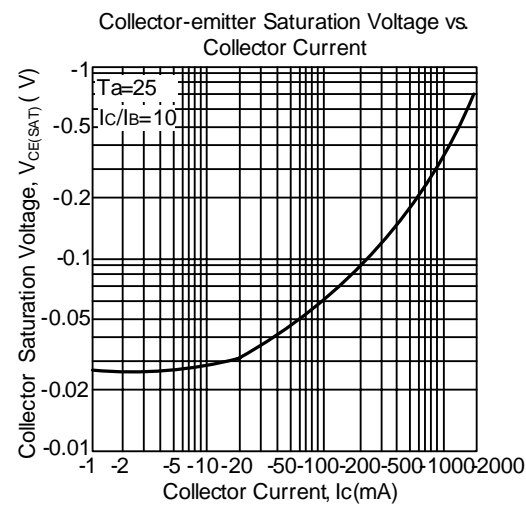
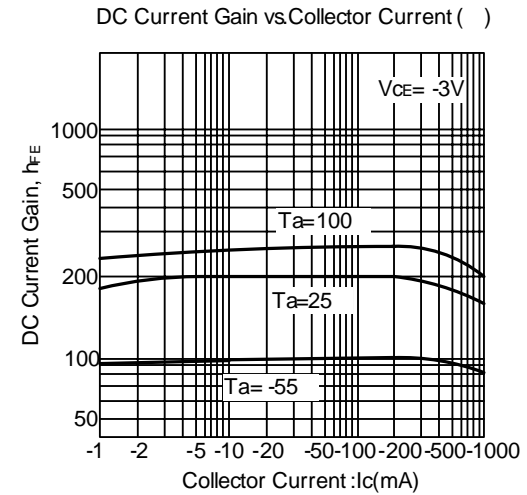
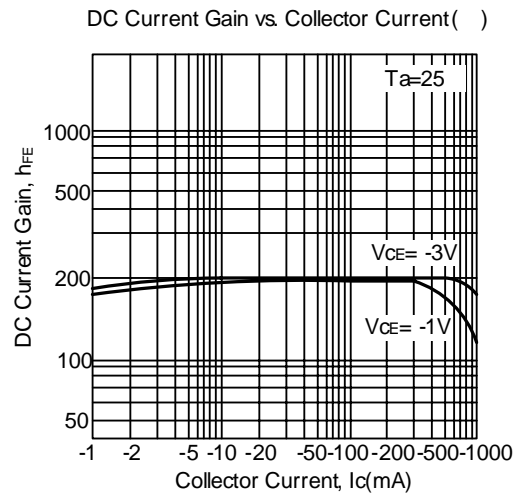
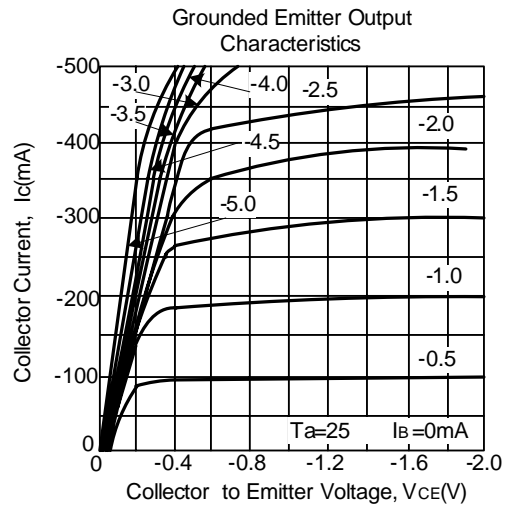
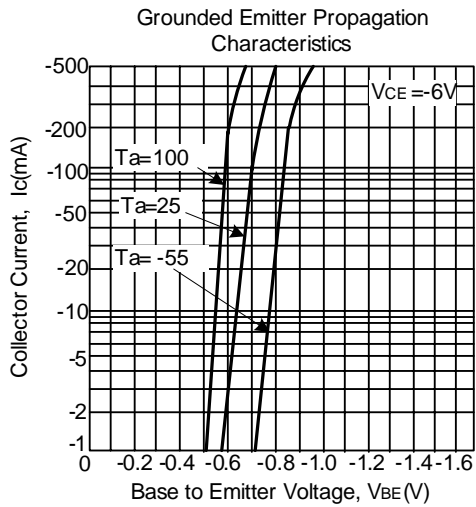
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector Base Breakdown Voltage	BV <sub>CBO</sub>	I <sub>C</sub> = -50μA	-40			V
Collector Emitter Breakdown Voltage	BV <sub>CEO</sub>	I <sub>C</sub> = -1mA	-32			V
Emitter Base Breakdown Voltage	BV <sub>EBO</sub>	I <sub>E</sub> = -50μA	-5			V
Collector Cut-Off Current	I <sub>CBO</sub>	V <sub>CB</sub> = -20V			-0.5	μA
Emitter Cut-Off Current	I <sub>EBO</sub>	V <sub>EB</sub> = -4V			-0.5	μA
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	I <sub>C</sub> = -500mA, I <sub>B</sub> = -50mA (Note)		-0.2	-0.5	V
DC Current Transfer Ratio	h <sub>FE</sub>	V <sub>CE</sub> = -3V, I <sub>C</sub> = -0.1A (Note)	82		390	
Transition Frequency	f <sub>T</sub>	V <sub>CE</sub> = -5V, I <sub>E</sub> = 50 mA, f=30MHz		150		MHz
Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> = -10V, I <sub>E</sub> = 0A, f=1MHz		20	30	pF

Note: Measured using pulse current.

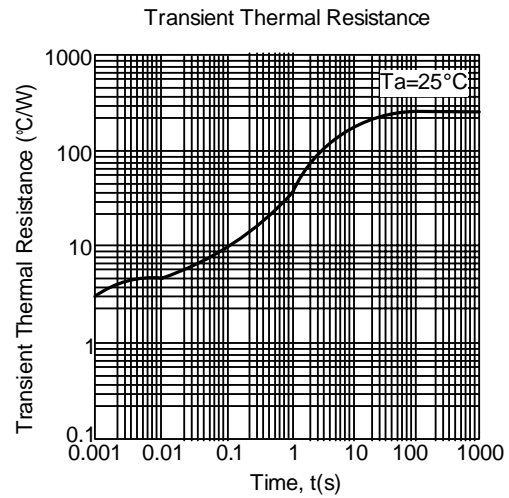
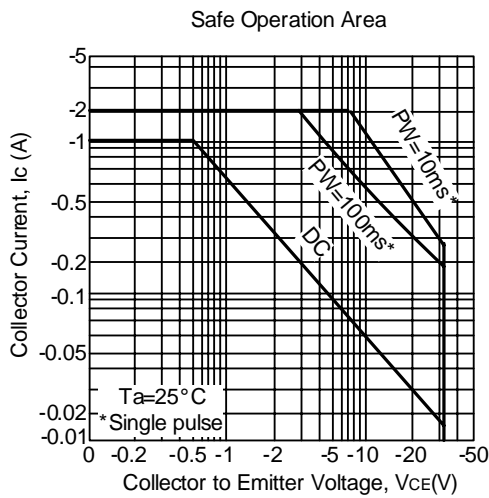
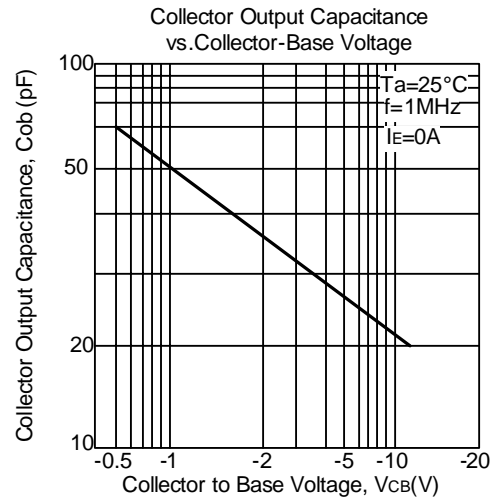
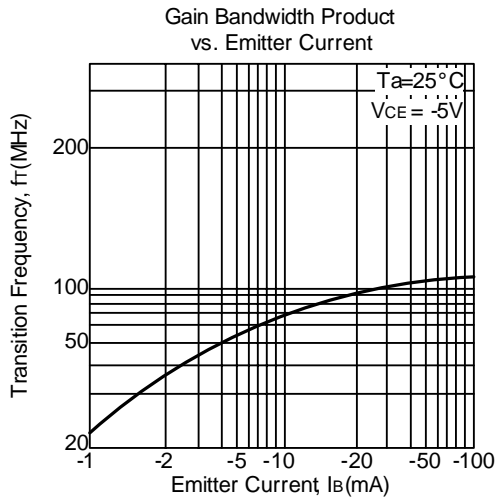
■ CLASSIFICATION OF h<sub>FE</sub>

RANK	P	Q	R
RANGE	82-180	120-270	180-390

## TYPICAL CHARACTERISTICS



## ■ TYPICAL CHARACTERISTICS(Cont.)



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